MSB92ASWT1G, MSB92AS1WT1G

PNP Silicon General Purpose High Voltage Transistor

This PNP Silicon Planar Transistor is designed for general purpose amplifier applications. This device is housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

Features

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	-300	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	-300	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	-5.0	Vdc
Collector Current – Continuous	I _C	500	mAdc
Electrostatic Discharge	ESD	HBM > 16,000, MM > 2,000	V

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	P _D	150	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

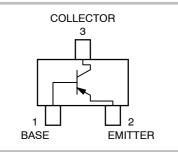
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.



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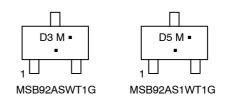
http://onsemi.com





SC-70 (SOT-323) CASE 419 STYLE 3

MARKING DIAGRAM



Dx = Device Code
M = Date Code*
• = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MSB92ASWT1G	SC-70 (Pb-Free)	3000/Tape & Reel
MSB92AS1WT1G	SC-70 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}Date Code orientation may vary depending upon manufacturing location.

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ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage (I _C = -1.0 mAdc, I _B = 0)	V _(BR) CEO	-300	_	Vdc
Collector-Base Breakdown Voltage ($I_C = -100 \mu Adc, I_E = 0$)	V _(BR) CBO	-300	_	Vdc
Emitter-Base Breakdown Voltage $(I_E = -100 \mu Adc, I_E = 0)$	V _{(BR)EBO}	-5.0	_	Vdc
Collector-Base Cutoff Current (V _{CB} = 300 Vdc, I _E = 0)	Ісво	-	-0.25	μΑ
Emitter–Base Cutoff Current $(V_{EB} = -3.0 \text{ Vdc}, I_B = 0)$	I _{EBO}	-	-0.1	μΑ
DC Current Gain (Note 2) $ \begin{array}{l} (V_{CE}=-10~\text{Vdc},I_{C}=-1.0~\text{mAdc})\\ (V_{CE}=-10~\text{Vdc},I_{C}=-10~\text{mAdc})\\ (V_{CE}=-10~\text{Vdc},I_{C}=-30~\text{mAdc}) \end{array} $	h _{FE1} h _{FE2} h _{FE3}	120 40 25	200 - -	-
Collector-Emitter Saturation Voltage (Note 2) (I _C = -20 mAdc, I _B = -2.0 mAdc)	V _{CE(sat)}	-	-0.5	Vdc
Base–Emitter Saturation Voltage (I _C = -20 mAdc, I _B = -2.0 mAdc)	V _{BE(sat)}	-	-0.9	Vdc
SMALL SIGNAL CHARACTERISTICS	•	•	•	•
Current – Gain – Bandwidth Product (I _C = -10 mAdc, V _{CE} = -20 Vdc, f = 20 MHz)	f _T	50	_	MHz

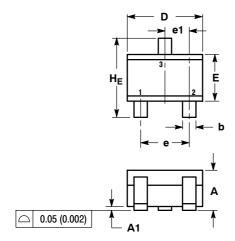
Current – Gain – Bandwidth Product (I _C = –10 mAdc, V _{CE} = –20 Vdc, f = 20 MHz)	f _T	50	-	MHz
Collector-Base Capacitance (V _{CB} = -20 Vdc, I _E = 0, f = 1.0 MHz)	C _{cb}	-	6.0	pF

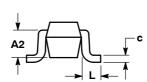
^{2.} Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

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PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 ISSUE N





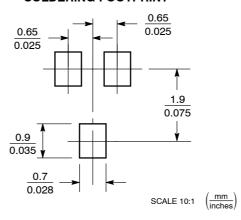
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BSC	;
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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